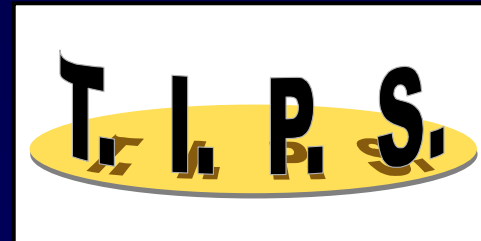


# Extending Cantilevered Probe Card Life An “Abrasive” Approach

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# Overview

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- Introduction
- Objectives / Approach
- Methodology Overview
- Implementation / Characterization
- End-User Customer Application
- Summary

# Objectives

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- Develop a systematic approach to improve cantilevered probe performance.
  - Economics and cycle time make cantilevered probe cards the most commonly utilized probe technology
- Characterize a methodology for extending cantilevered probe card life.
- Demonstrate improvements in probe card performance as well as probe card service life.
  - Assess the applicability to “best” wafer level test practices for specific end-user customers.

# Approach

- Consider some basic concepts from spot welding
  - Re-visit the empirical model proposed by Babu, et. al (2001)

$$C_{\text{RES}} = \frac{(\rho_{\text{pad}} + \rho_{\text{probe}})}{4} \left[ \left( \frac{\pi \sigma_{\text{YS}}}{\eta P} \right)^{1/2} + \frac{3\pi}{4\eta^{1/2}} \right] + \frac{\rho_{\text{film}}}{a\eta\pi}$$

- $\rho_{\text{pad}}$ ,  $\rho_{\text{probe}}$ ,  $\rho_{\text{film}}$  = resistivity values
  - $\sigma_{\text{YS}}$  = material yield strength
  - $P$  = contact pressure
  - $a$  = average radius of contacting asperities, or *a-Spot* size
  - $\eta$  = number density of *a-Spots* that are in real contact
- Contact pressure ( $P$ ) is the applied force normalized by true contact area
  - $\eta$ ,  $a$  depend on the surface roughness of the contacting solids

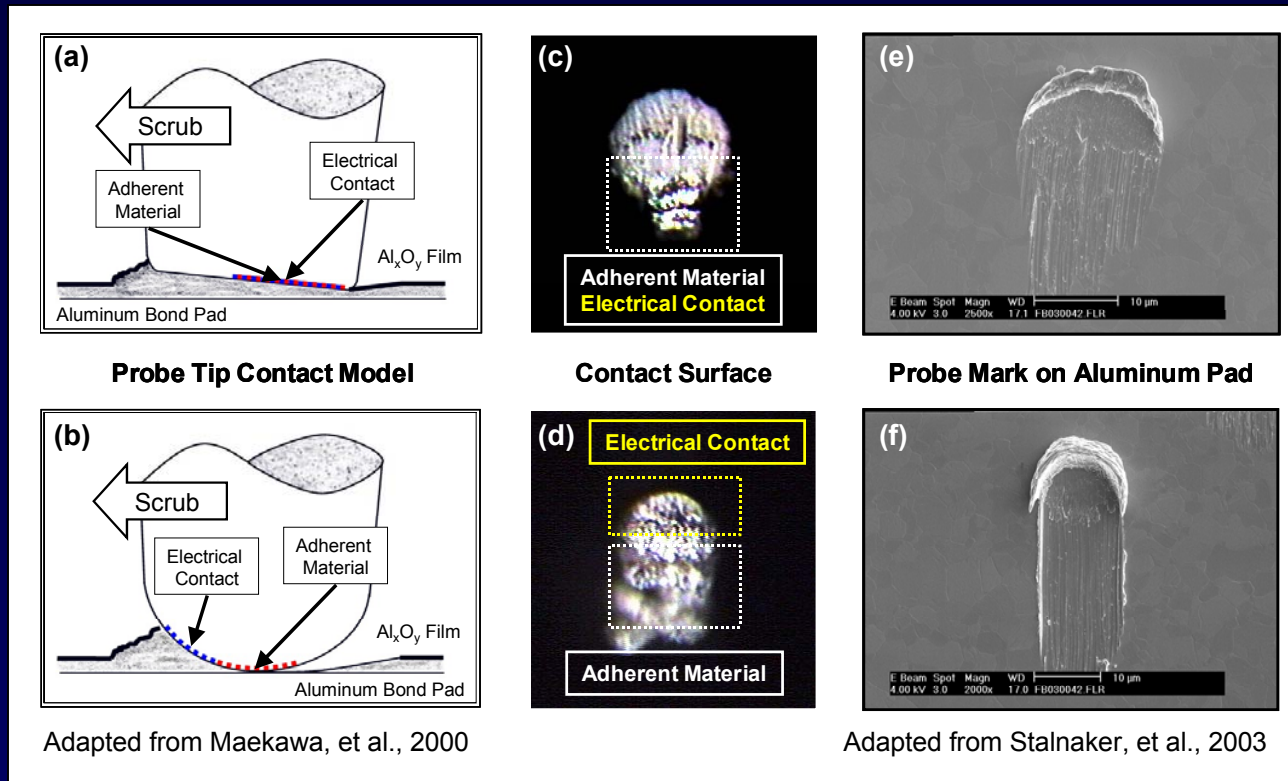
# Approach (cont.)

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- Critical factors with applicability to cantilever probes.
  - Presence of contamination, e.g. oxides, residues, etc.
    - Probe tip shape plays an important role in displacing the contaminants from the true contact area
    - On-line cleaning methods can be used to “control” adherent contaminants and remove debris
  - True Contact Area =  $\mathcal{F}$  (Tip Shape, Applied Force, Surface Finish)
    - *True* contact area of a flat tip probe is “large”; however, the applied pressure and *a-Spot* density are “low”
    - *True* contact area of a radius tip probe is “small”; however, the applied pressure and *a-Spot* density are “large”
  - Asperity density depends on the microscopic surface roughness
    - Smooth surfaces have a high asperity density
    - The increase in asperity density decreases the electrical  $C_{RES}$
    - A “rough” finish facilitates material accumulation on contact surface.

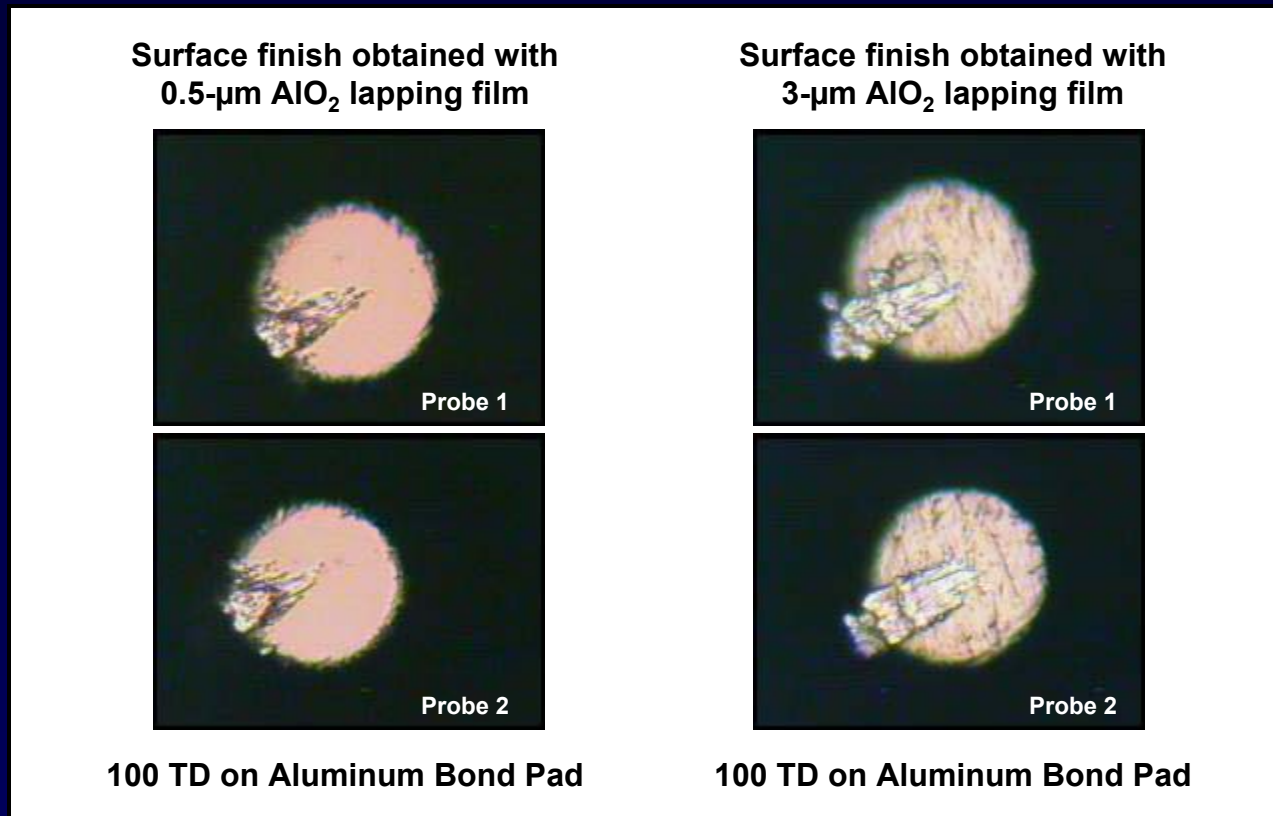
# Physical Contact Mechanisms

- A smooth, rounded tip allows the bond pad to deform easily around the probe tip and contact surface.
- Electrical contact region of the rounded shape is at the leading edge and across a smooth, “relatively clean” surface.



# Effect of Surface Roughness

- Surface roughness affects pad material accumulation.



- Flat, tipped probes with a TOO smooth surface finish will not properly penetrate the bond pad surface oxides.

# Probe Tip Shape Factors

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- Rounded and radius tipped, cantilevered probes have shown advantages over flat tips for wafer sort.
  - More stable contact resistance
  - A smooth surface finish that penetrates the surface oxides
  - Smaller probe marks and reduced pad damage
  - Reduced need for on-line cleaning
  - Probe tip maintenance can be achieved using proven non-destructive on-cleaning practices
- As with any technology there are some disadvantages.
  - Higher unit pressure, may require a reduction in probe force
  - Potential for deeper probe marks that could damage underlying IC stack
  - Reduced reflective probe tip area that may require modifications of algorithms on the prober and analyzer
  - “Standard” on-line / off-line abrasive cleaning damages the probe shape



# Developing a Rounded Tip Shape

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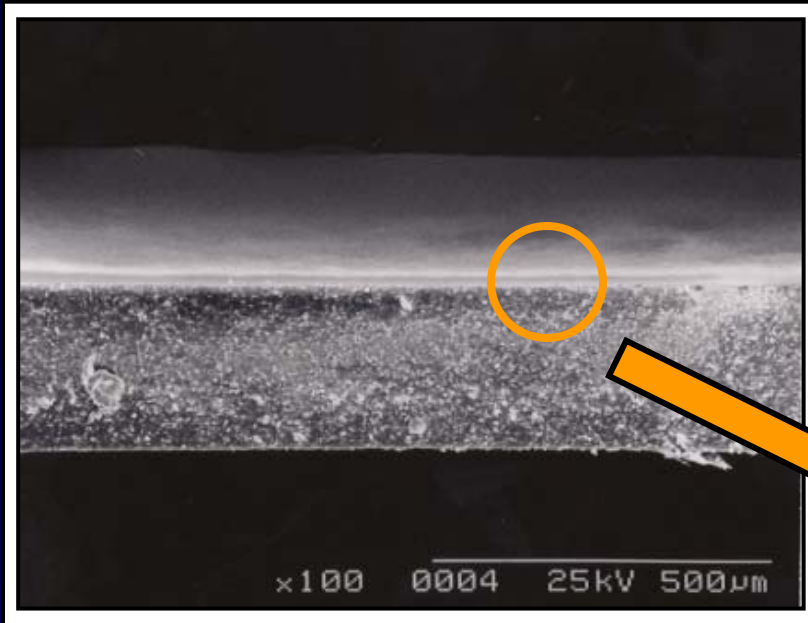
- Electrochemical machining and polishing
  - “Gang Process” – the probe card is built with shaped tip probes
    - Probes must be “tweaked” into specification without lapping operations.
    - Extra care must be taken to avoid damaging the tip shape.
  - “In Spider” – probes are shaped after the probe card has been built
    - Manual etch operation in which probes are individually radiused by an experienced technician; however, the tip shapes can be inconsistent.
    - Probe tips are “etched” *in-situ*; however, damage can occur to the PCB due to capillary action (wicking) of the electro-chemicals.
    - Probe-to-Probe (tip shape, tip length, etc.) variability can occur.

# Developing a Rounded Tip Shape (cont.)

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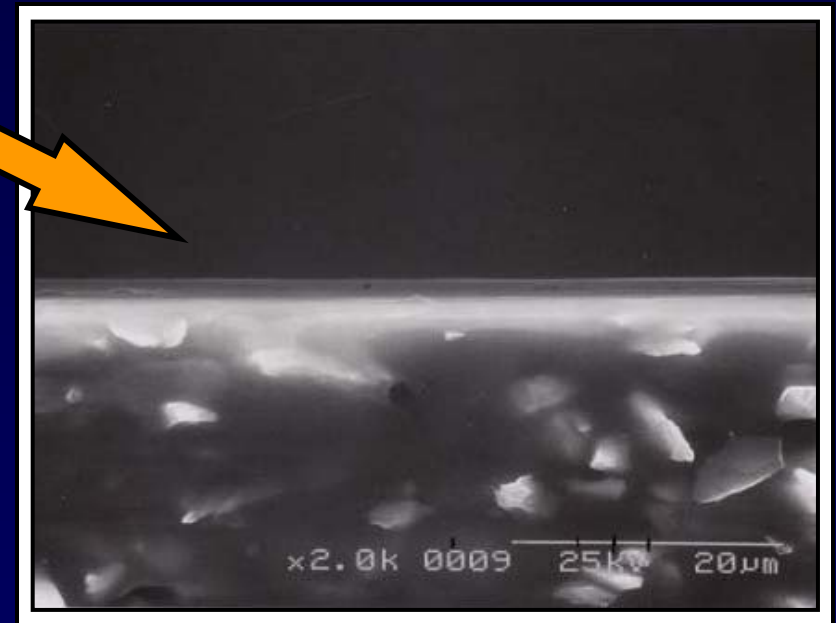
- Material removal using “abrasive” methods
  - Porous, “sponge-like” material impregnated with abrasive particles
    - Inconsistent and un-even material removal.
    - Structural properties of open-cell foam can cause significant tip sharpening.
  - Polymeric material, with spatially distributed abrasive particles
    - Polymer matrix provides uniform pressure distribution along tip length
    - Predictable material removal rates to attain semi-radius and fully radiused probe tips.

# Developing a Rounded Tip Shape (cont.)

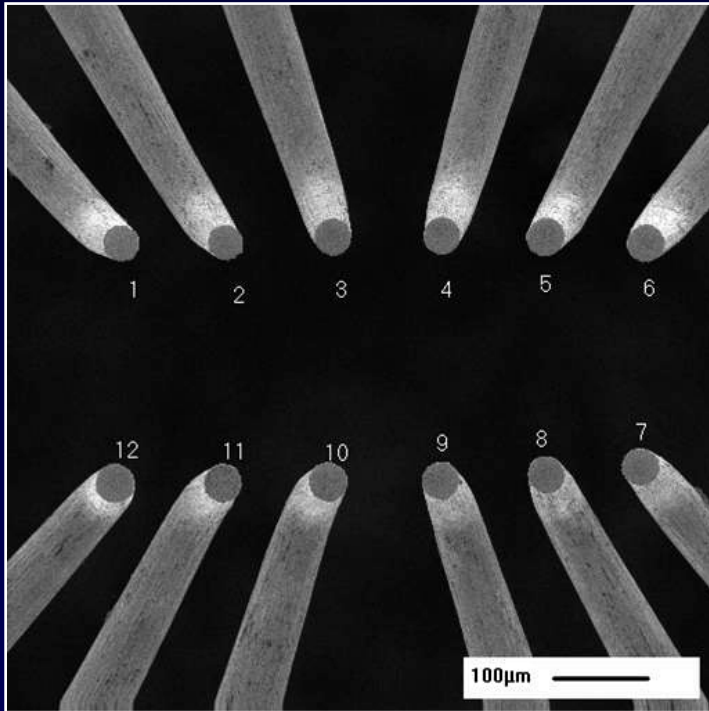


Highly cross-linked polymeric material  
(Probe Form™)

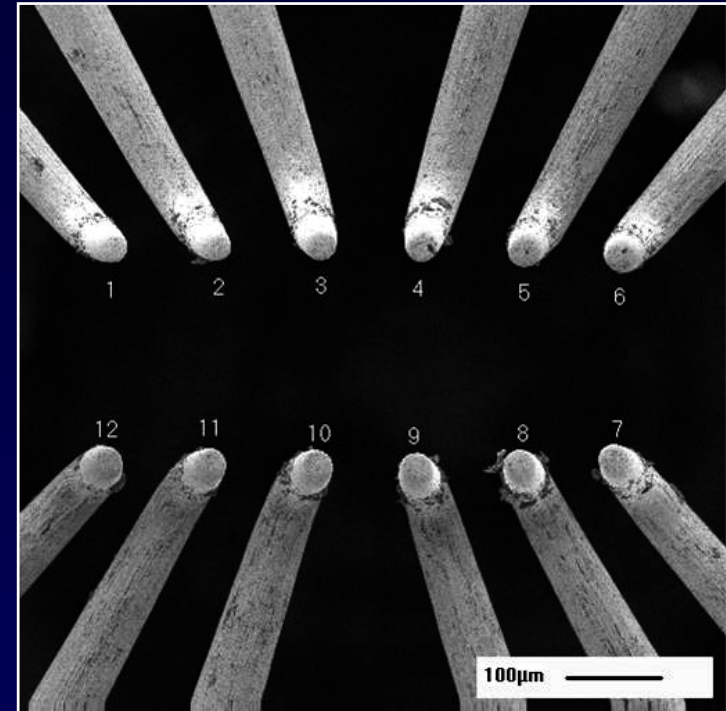
Spatially Distributed Abrasive Particles



# Developing a Rounded Tip Shape (cont.)



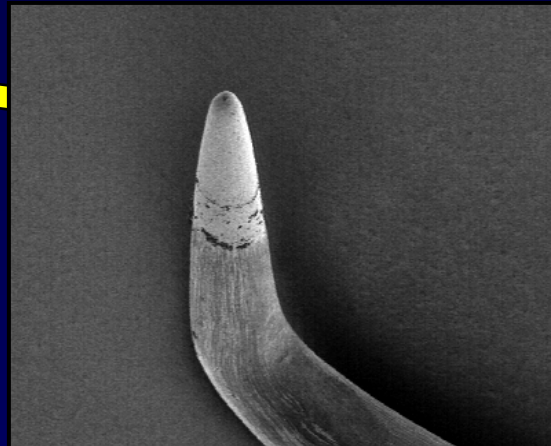
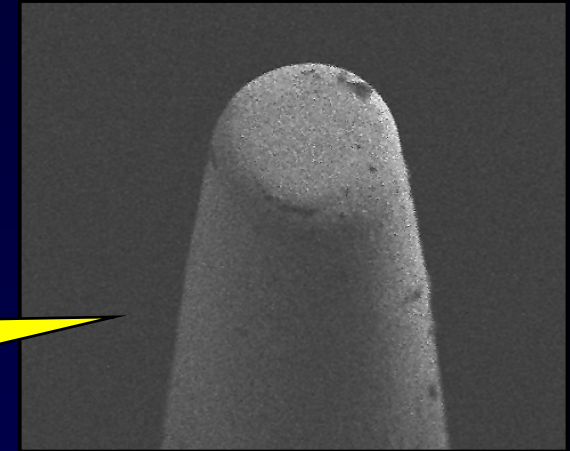
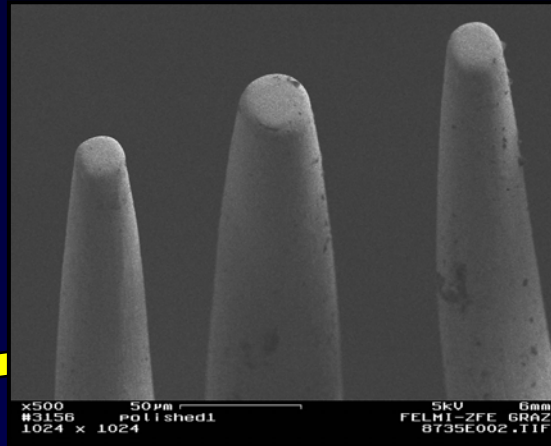
Tungsten-Rhenium (WRe)  
Flat Tip Probes (As Built)



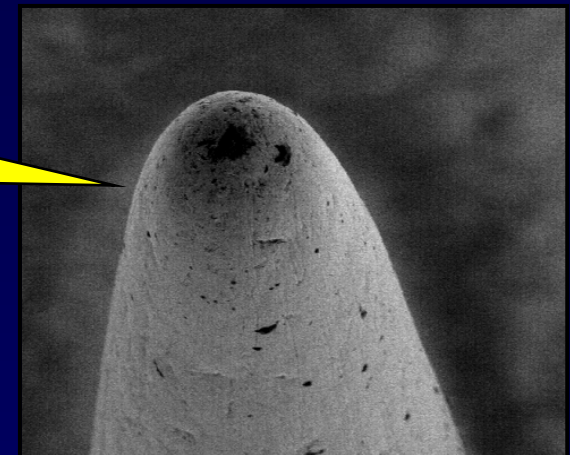
Reshaped to Semi-Radius Tip  
with Probe Form™

# Developing a Rounded Tip Shape (cont.)

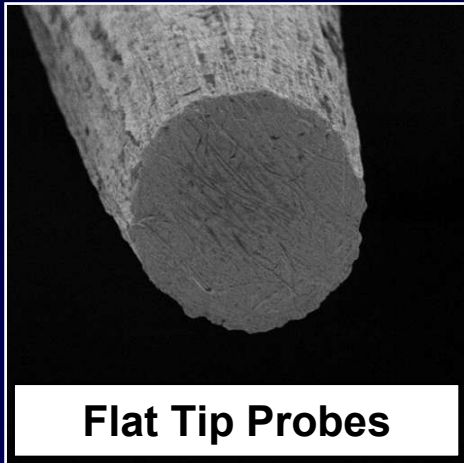
**Semi-Radius Tips**



**Full Radius Tips**

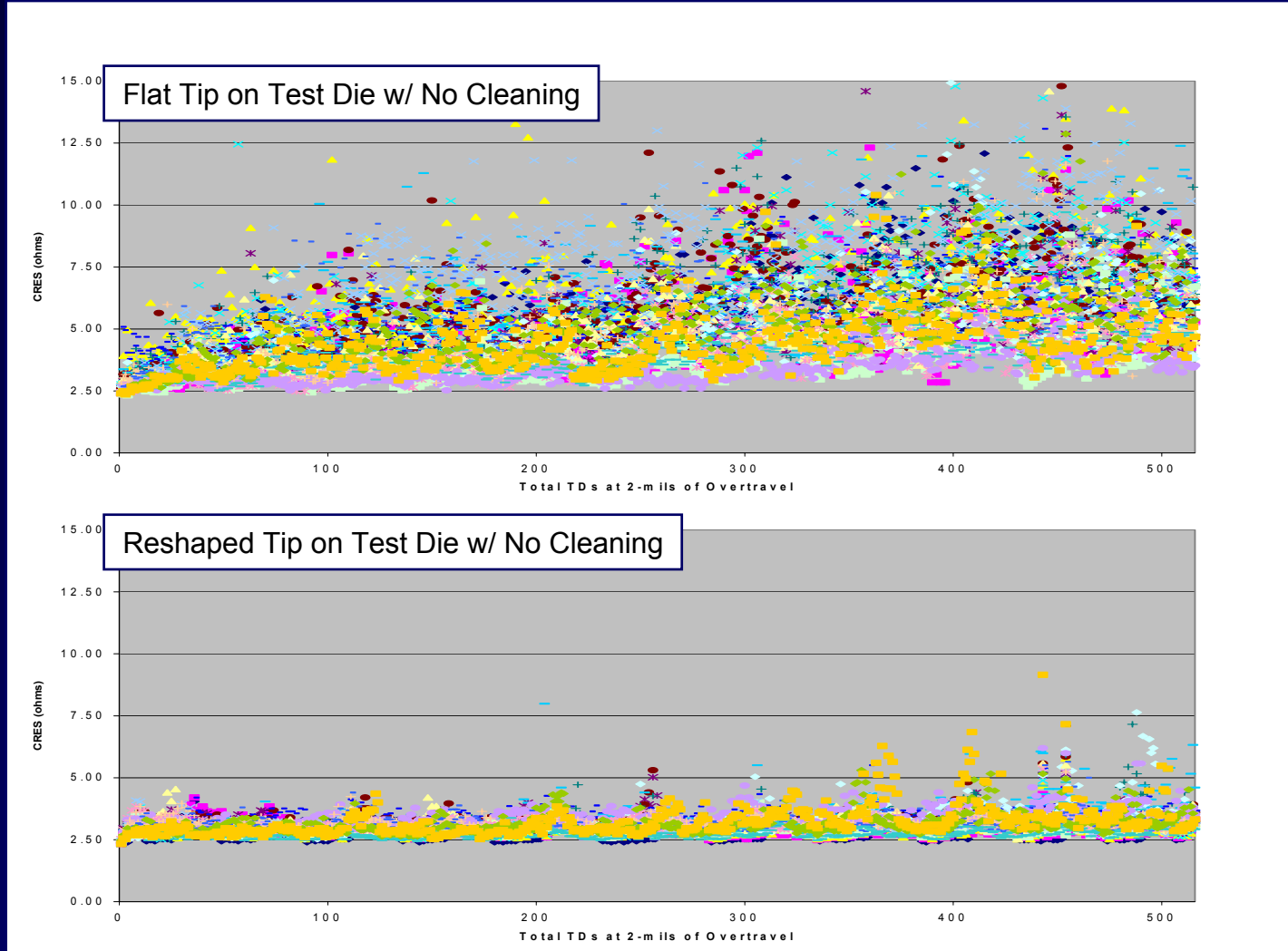


Radius tip images courtesy of AMI Semiconductor



**Flat Tip Probes**

# Rounded Tip Shape – CRES Stability

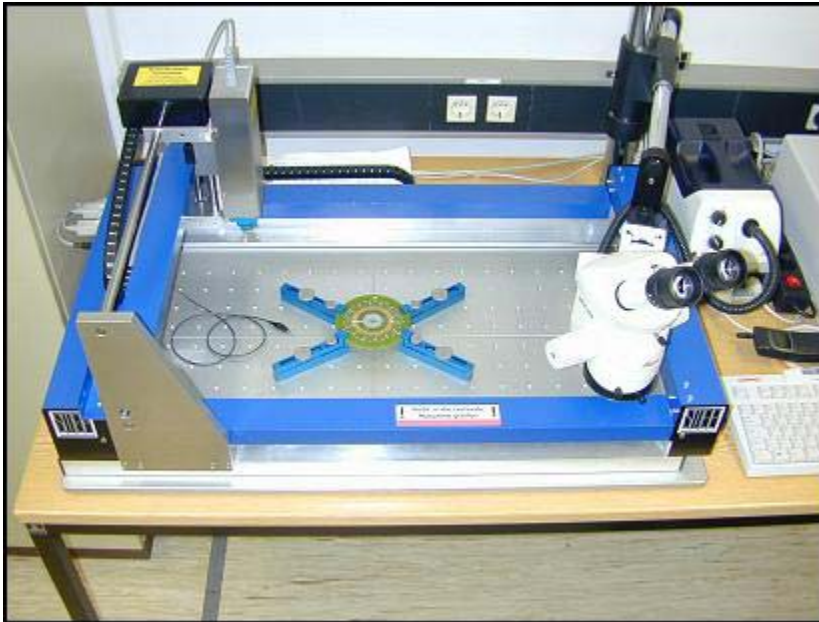




# Tip Shape Forming and “Refreshing”

- TPR02 – “Probe Refresher”
  - Computer controlled 3-axis stage with probe height sensor
  - Mobile microscope for probe tip inspection
  - Universal clamps accommodate probe-card types

System Overview

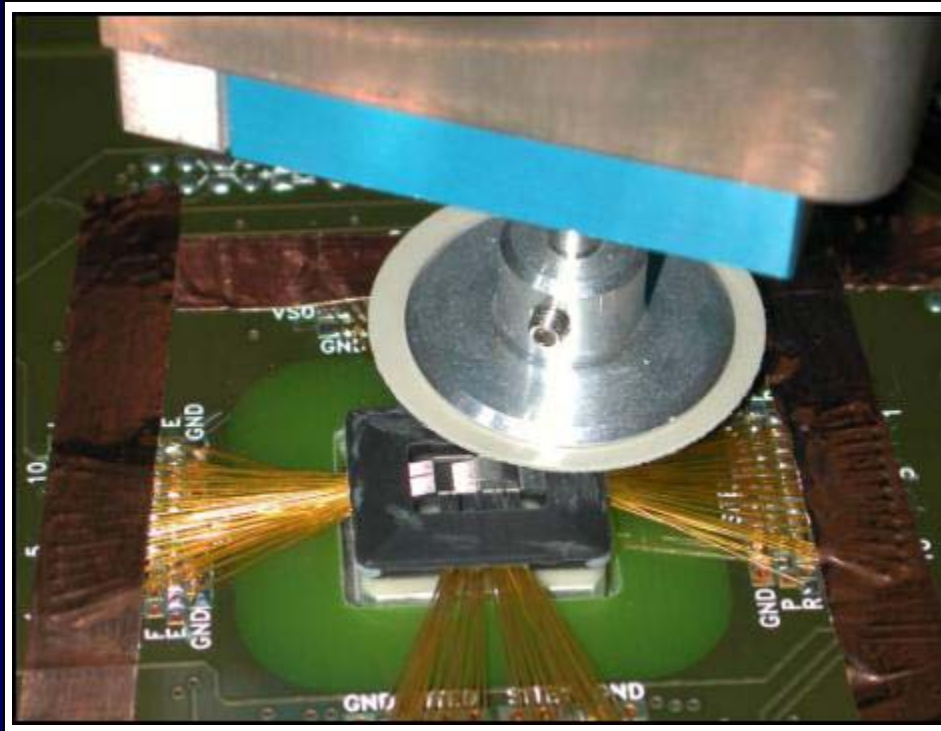


Fine Pitch Probe Card



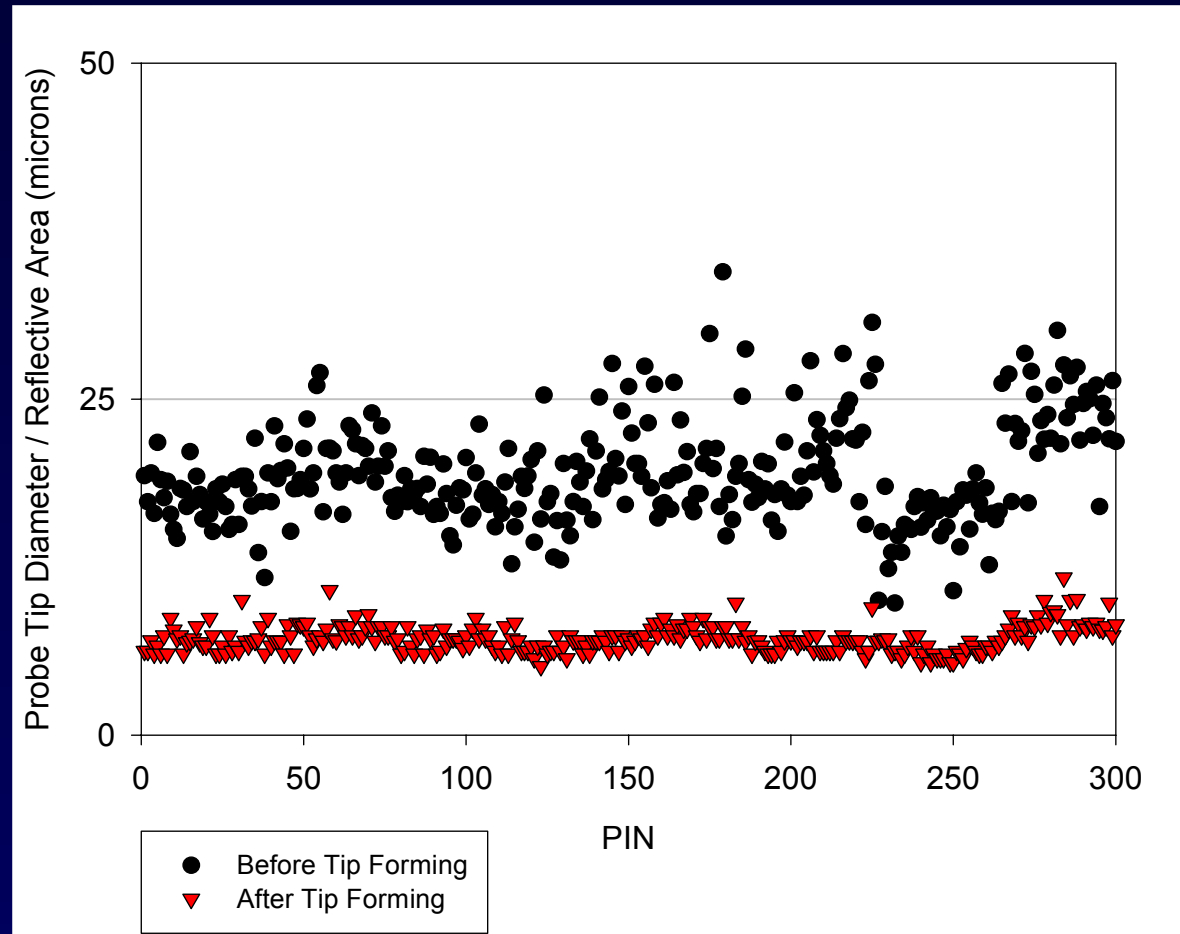
# Principle of Operation

- Grinding head equipped with Probe Form™
  - Probe tips repeatedly inserted into the elastomeric material.
  - Embedded aluminium and adherent debris from wafer is removed.
  - Probe tips are quickly shaped (or reshaped) and polished.

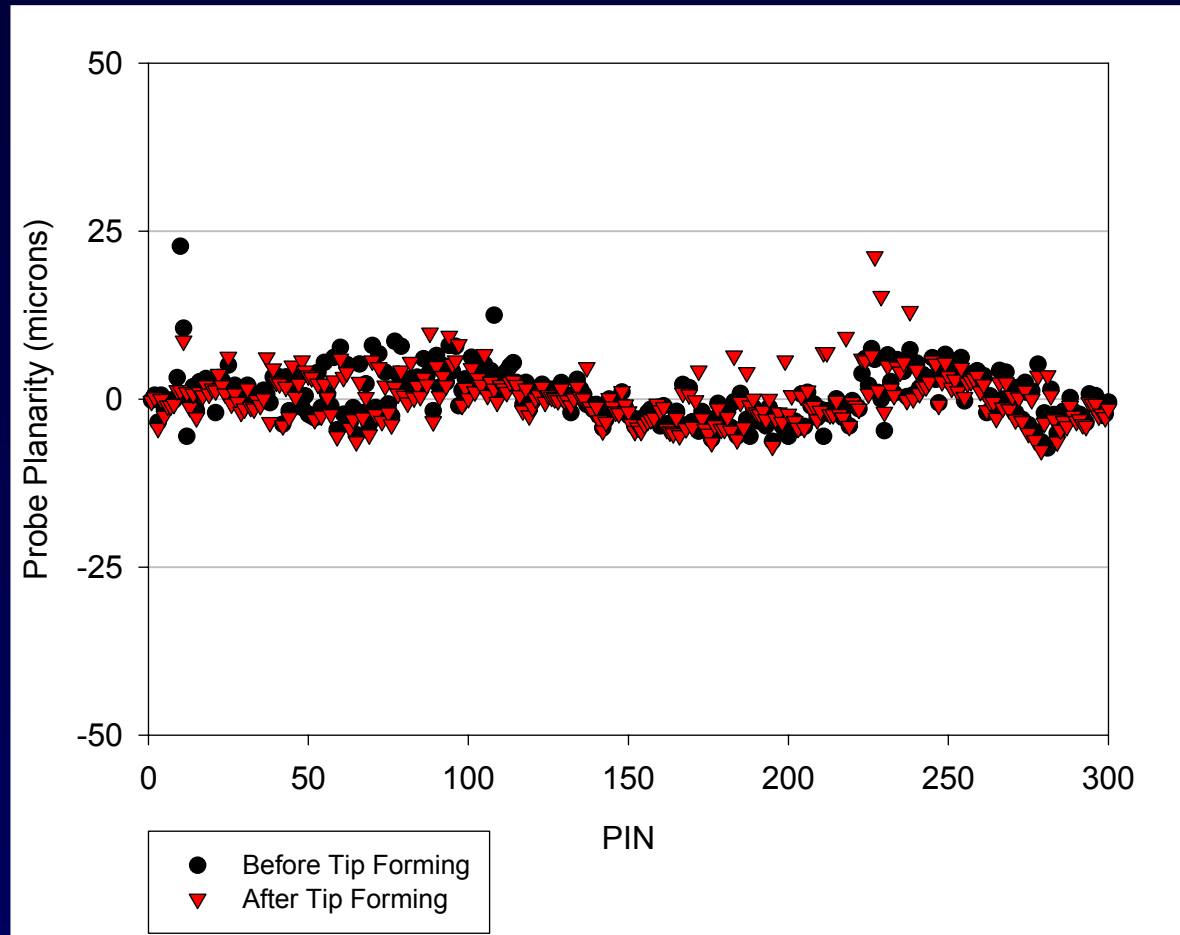




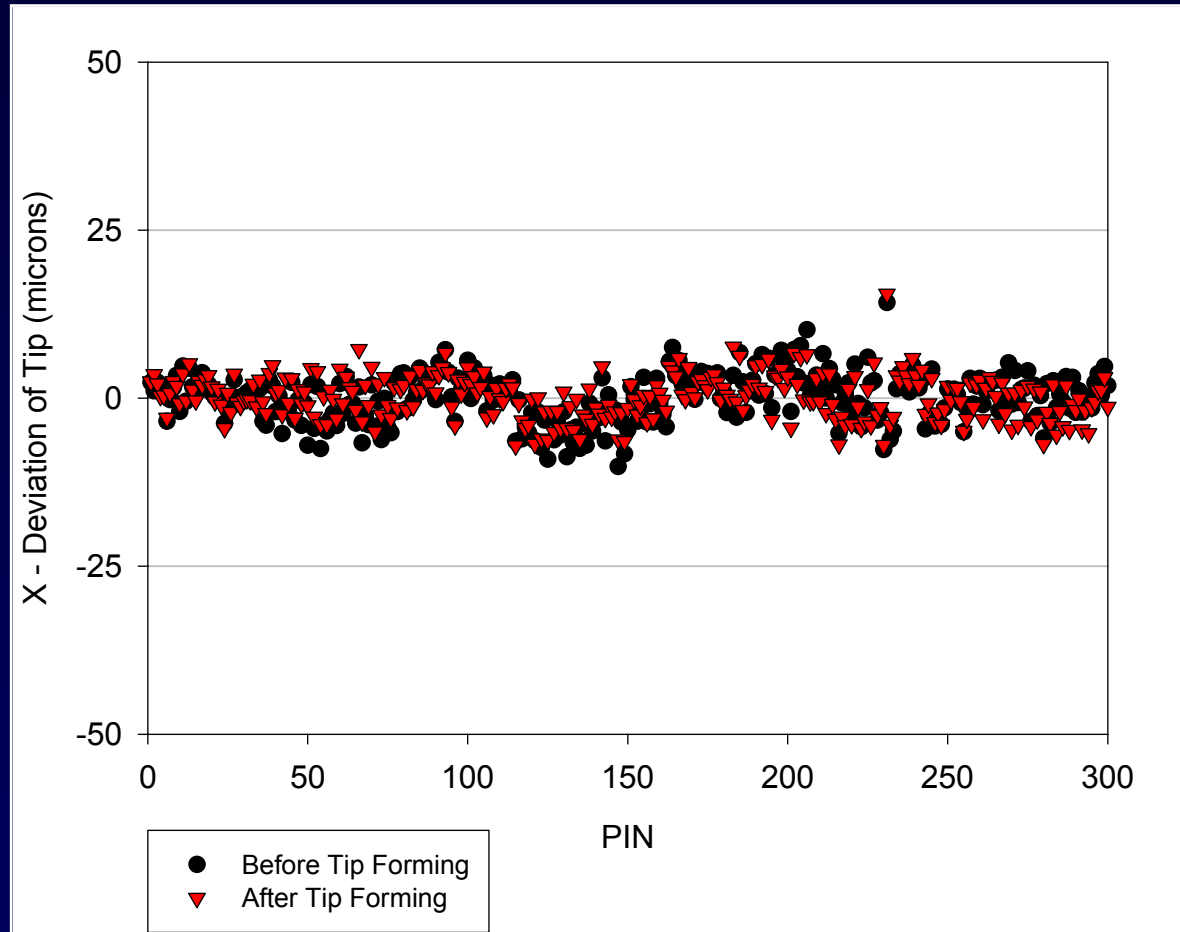
# Tip Diameter (Reflective Area) “Reduction”



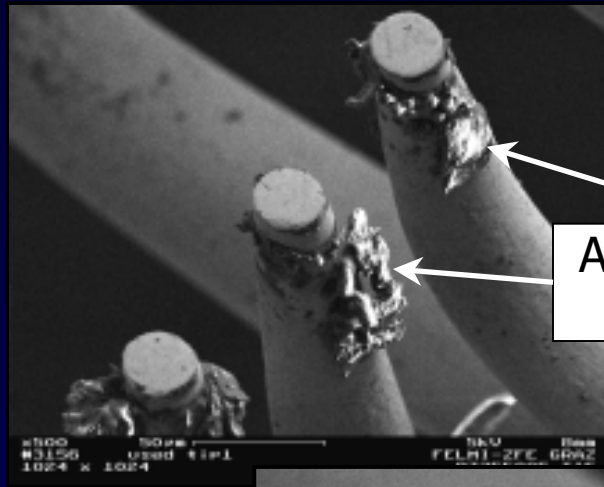
# (no) Effect on Planarity



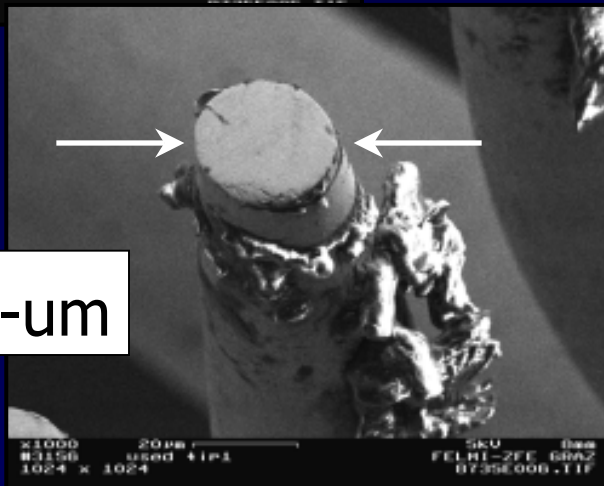
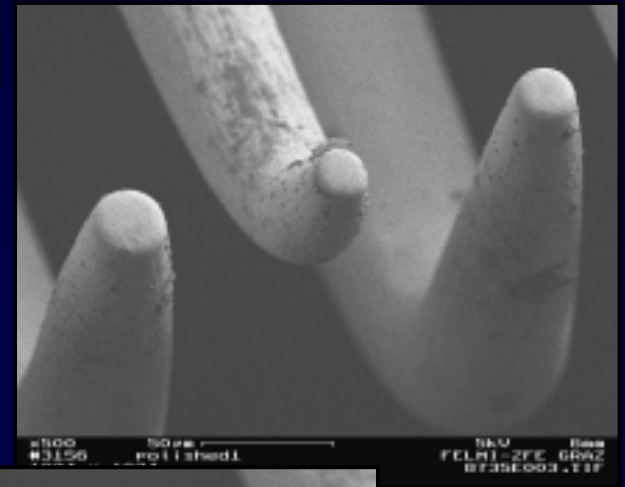
# (no) Effect on Probe Alignment



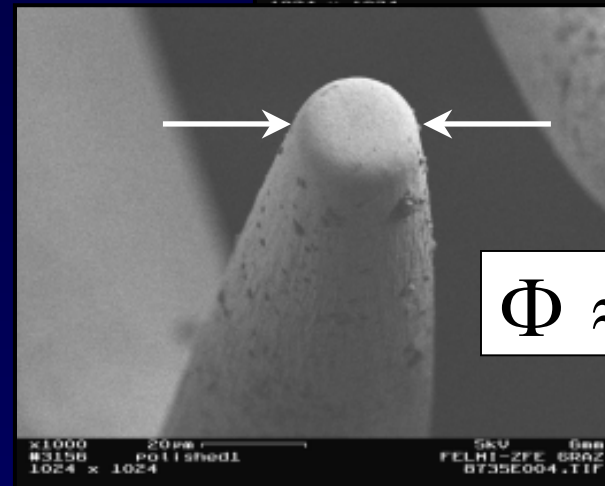
# “Refreshing” Fine Pitch Probe Tips



Adherent Bond Pad Debris

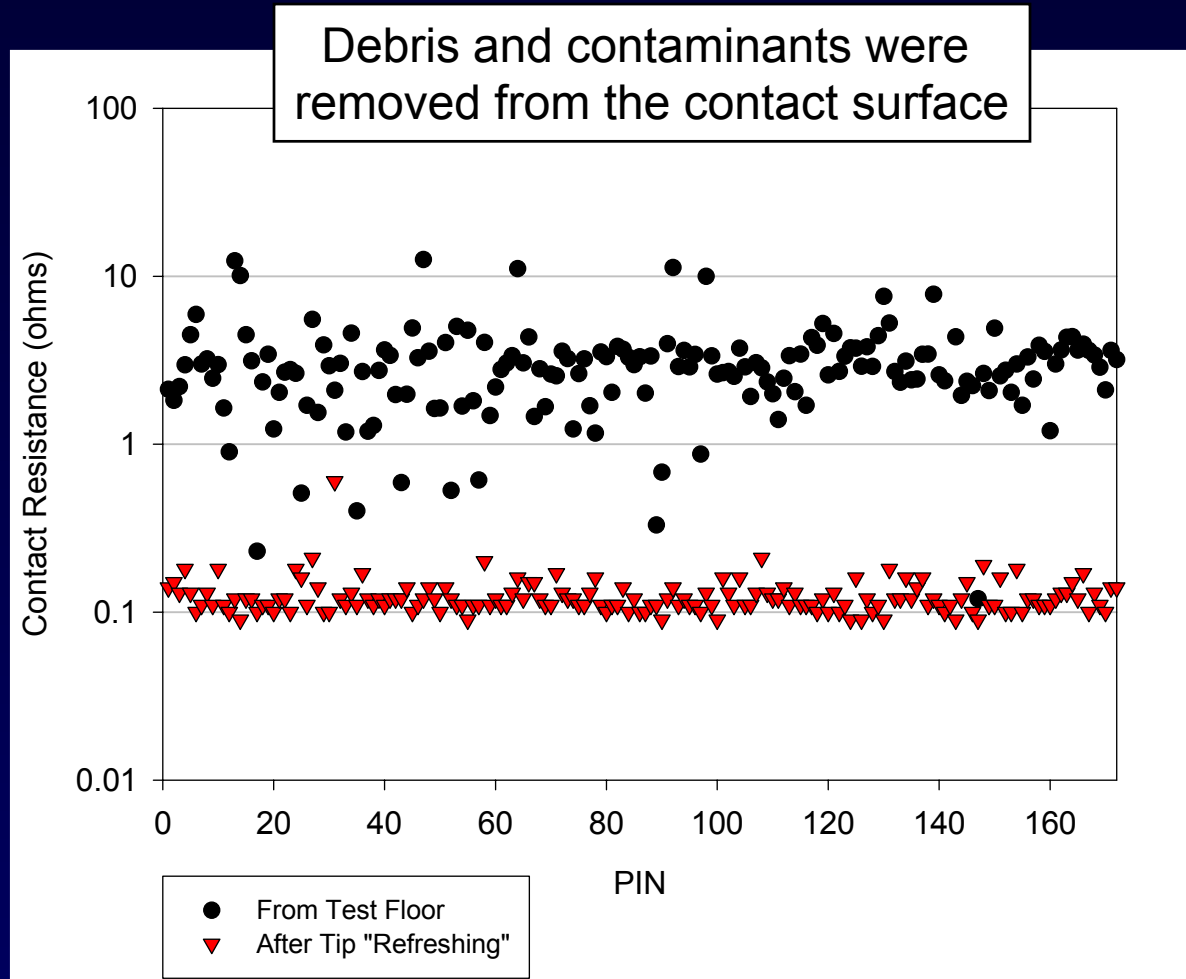


$\Phi \approx 25\text{-um}$

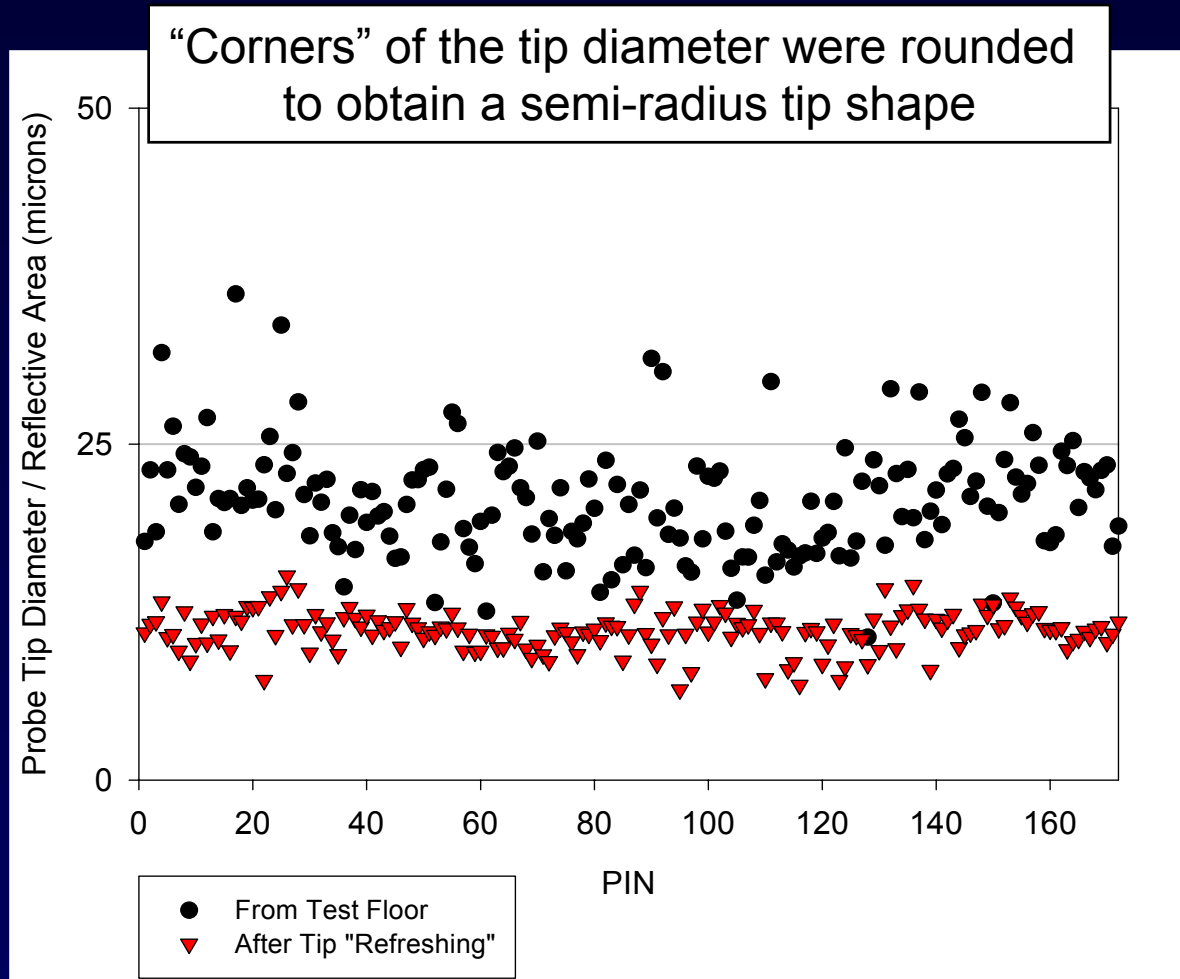


$\Phi \approx 16\text{-um}$

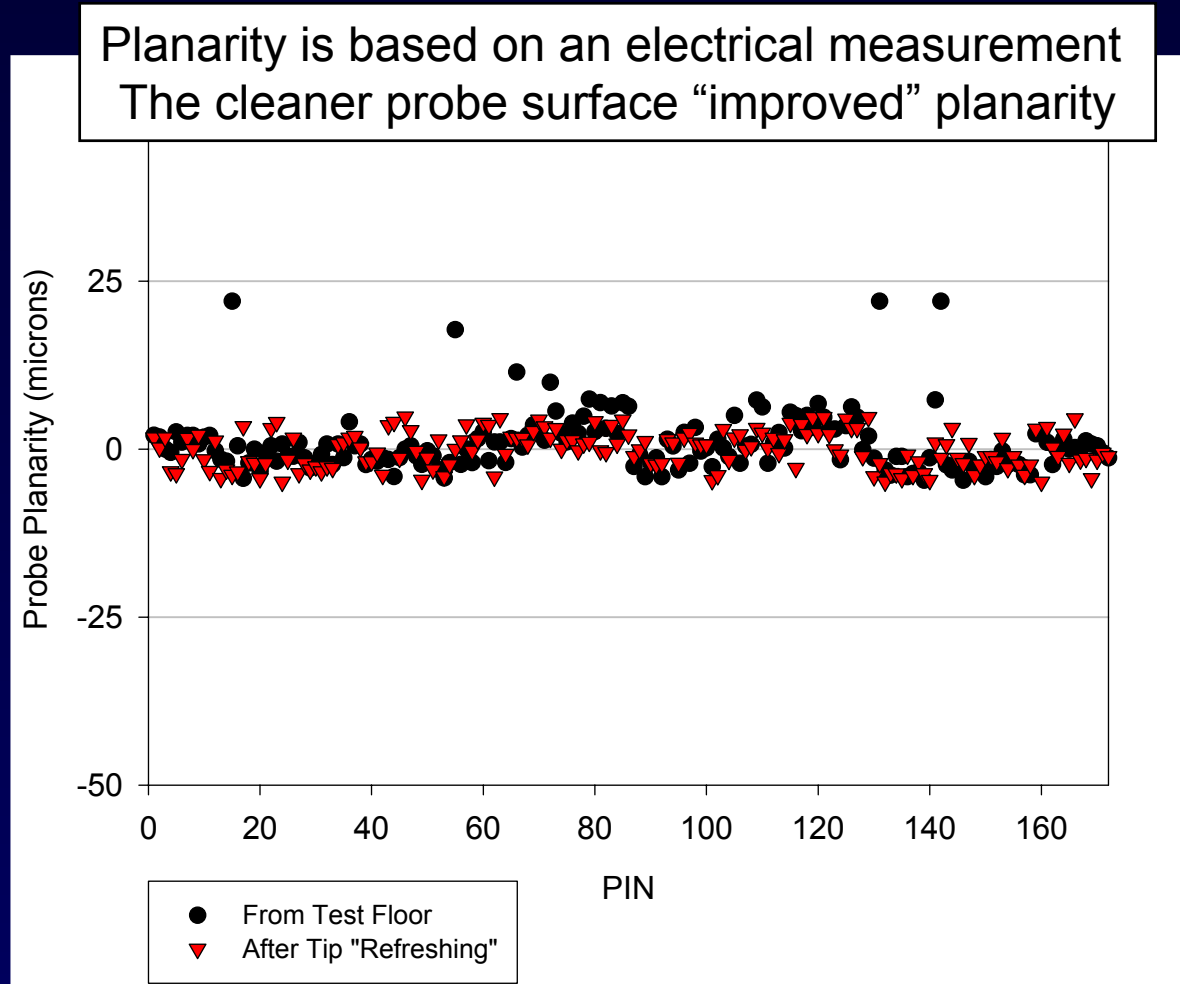
# Effect on Contact Resistance



# Tip Diameter (Reflective Area) "Reduction"

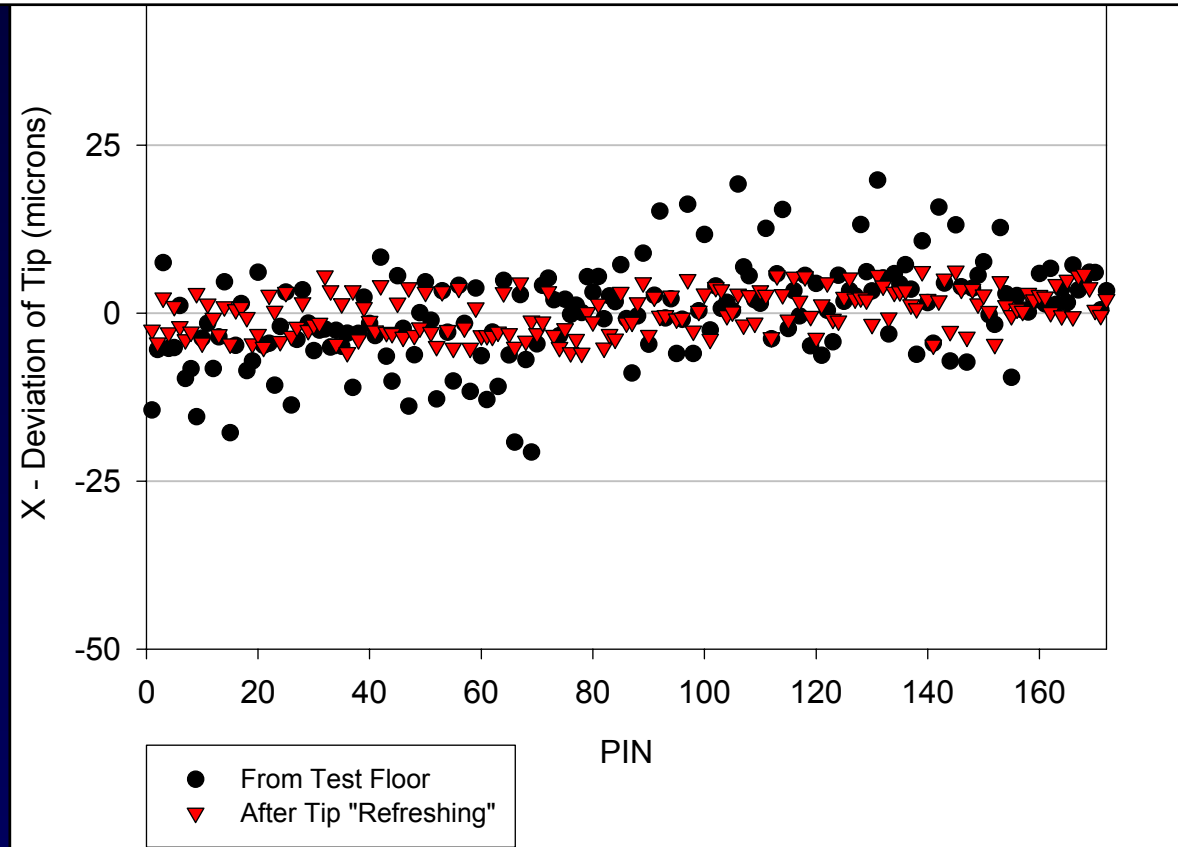


# (some) Effect on Planarity



# (some) Effect on Alignment

Alignment is based on optical measurements  
Removal of adherent pad materials "improved" alignment





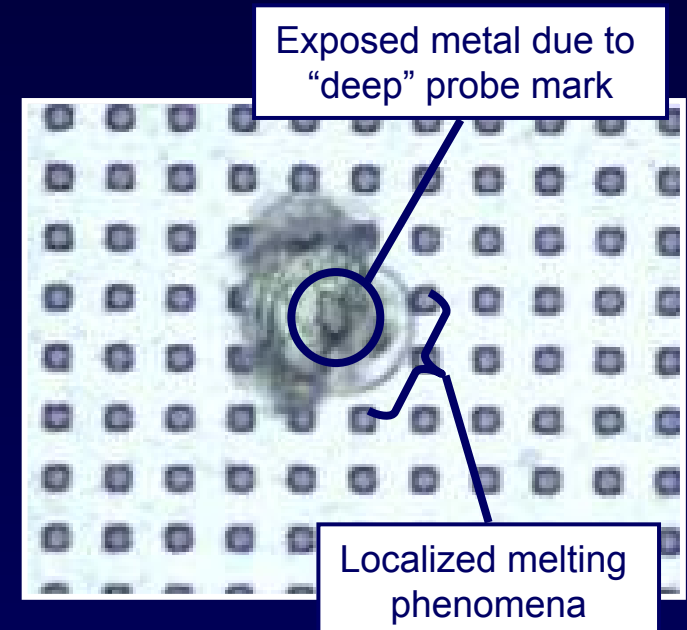
# Design Considerations / Limitations

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- Bearing stresses (force / unit area) exerted by shaped probes are substantially greater than those of flat tip probes.
  - Estimate as much as 35X greater applied bearing stress.
  - Probe force can be reduced without affecting performance
- Shaped probes could “dig too deep” into the bond pad.
  - Shear forces and stress distribution imparted to the bond pad during the “scrubbing action” may cause damage to the underlying structures.
  - Barrier metal or bare silicon could be exposed; thereby, resulting in assembly and reliability issues.
- Structural characteristics and load bearing capacity of the IC device must be considered.
  - Pads over active area (POAA), e.g., power semiconductor testing.
  - Low-k dielectric layers are more fragile and could be damaged.
  - High current applications can have higher contact temperatures due to localized Joule heating phenomena

# End-User Customer Application

- High current automotive wafer test
  - Flat-tipped probe geometry
    - Contact quality degraded quickly requiring frequent cleaning and maintenance
  - Radius-tipped probe geometry
    - High current densities and localized Joule heating observed
    - Damage to underlying structures
  - Semi-radius tipped probe geometry
    - Consistent electrical contact
    - Maintained off-line with the TPR02
    - Non-destructive on-line cleaning to collect debris and adherent material



# Summary

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- A systematic approach was utilized to further understand cantilevered probe tip contact mechanisms and electrical performance characteristics.
- Improvements in probe card performance and service life were realized through off-line probe tip shape forming and “refreshing” practices.
- Design considerations for probe bearing stress, resultant probe mark depth, and user application are needed to avoid damage to the underlying structures.
- Appropriate on-line cleaning solutions are required to properly maintain a tip shape for optimal electrical performance.

# Acknowledgements

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- Jerry Broz, Ph.D., ITS Applications Engineering
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- End-user customers that must remain anonymous

**Thank you for your attention**

**Questions ???**